

Rev.02 - 29 May 2018

Product data sheet

1. General description

High voltage, high speed, planar passivated NPN power switching transistor with integrated anti-parallel emitter-collector diode in a SOT54 (TO-92) plastic package.

2. Features and benefits

- High typical DC current gain
- Fast switching
- High voltage capability
- Integrated anti-parallel E-C diode

3. Applications

- Compact fluorescent lamps (CFL)
- Low power electronic lighting ballasts
- Off-line self-oscillating power supplies (SOPS) for battery charging

4. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
V_{CESM}	collector-emitter peak voltage	V _{BE} = 0 V		7	00		V
I _C	collector current	DC	1.5		А		
P _{tot}	total power dissipation	T _{lead} ≤ 25 °C; <u>Fig. 1</u>	2.1		W		
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
h _{FE}	DC current gain	I _c = 0.5 A; V _{ce} = 2 V; T _i = 25 °C		8	17	25	

5. Pinning information

Table 2.	Pinning infor	mation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		C I
2	С	collector		
3	E	emitter	() (E sym131

6. Ordering information

Table 3. Ordering inform	nation		
Type number	Package		
	Name	Description	Version
PHD13003C	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

7. Limiting values

Table 4. Limiting values

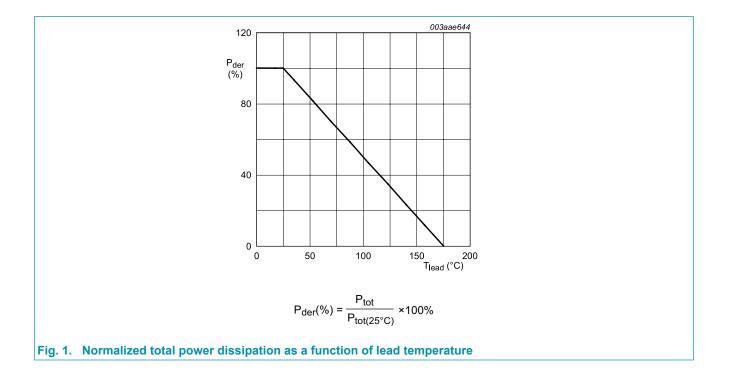
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{CESM}	collector-emitter peak voltage	V _{BE} = 0 V	700	V
V _{CBO}	collector-base voltage	I _E = 0 A	700	V
V _{CEO}	collector-emitter voltage	I _B = 0 A	400	V
I _c	collector current	DC	1.5	А
I _{CM}	peak collector current		3	А
I _B	base current	DC	0.75	А
I _{BM}	peak base current		1.5	А
P _{tot}	total power dissipation	T _{lead} ≤ 25 °C; <u>Fig. 1</u>	2.1	W
T _{stg}	storage temperature		-65 to 150	°C
Tj	junction temperature		150	°C
V_{EBO}	emitter-base voltage	I _c = 0 A; I(Emitter) = 10 mA	9	V

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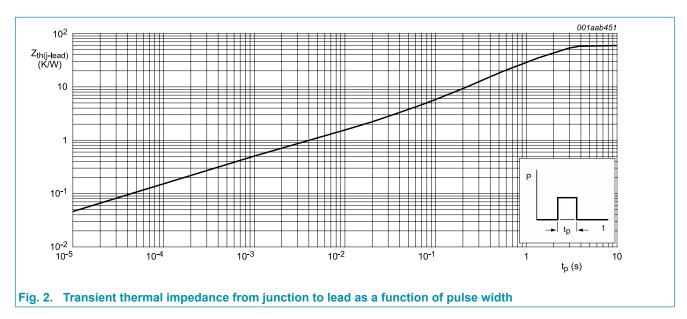
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8. Thermal characteristics

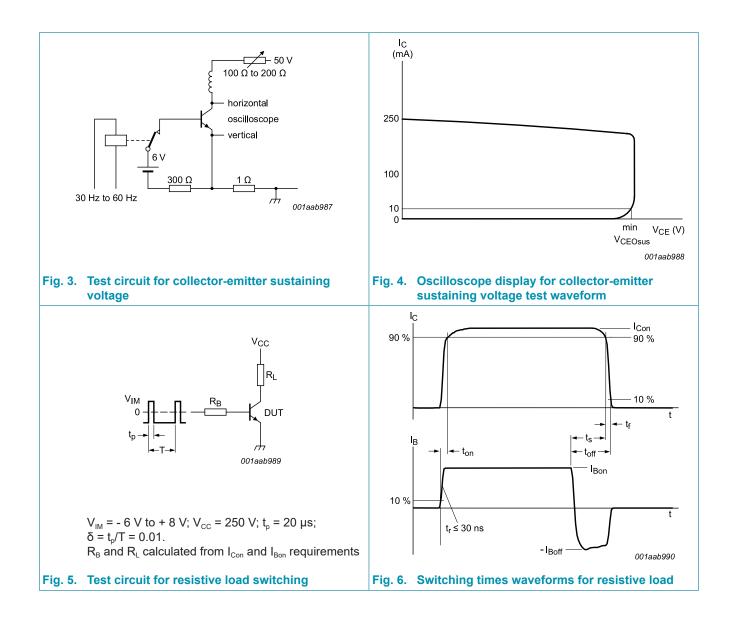
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	Fig. 2	-	-	60	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air; printed-circuit board mounted; lead length = 4 mm	-	150	-	K/W



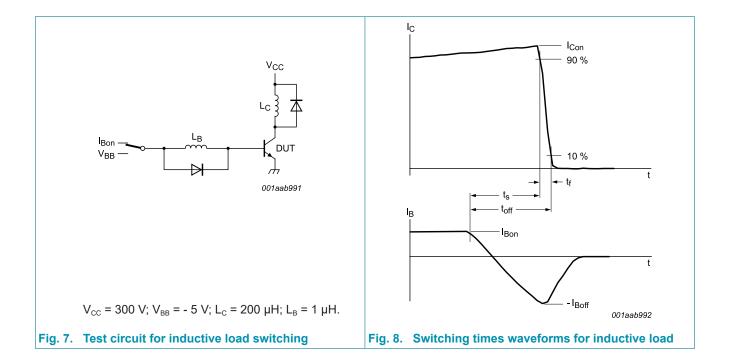
9. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics		I			
I _{CES}	collector-emitter cut-off	V _{BE} = 0 V; V _{CE} = 700 V	-	-	1	mA
	current	V _{BE} = 0 V; V _{CE} = 700 V; T _j =100°C	-	-	5	mA
I _{CEO}	collector-emitter cut-off current	V _{CE} = 400 V; I _B = 0 A; T _{lead} = 25°C	-	-	0.1	mA
I _{EBO}	emitter-base cut-off current	V _{EB} = 9 V; I _C = 0 A; T _{lead} = 25°C	-	-	1	mA
V_{CEOsus}	collector-emitter sustaining voltage	$I_B = 0 \text{ A}; I_C = 1 \text{ mA}; L_C = 25 \text{ mH};$ $T_{\text{lead}} = 25^{\circ}\text{C}; Fig. 3; Fig. 4$	400	-	-	V
V _{CEsat}	collector-emitter	I _C = 0.5 A; I _B = 0.1 A; T _{lead} = 25°C	-	-	0.5	V
	saturation voltage	$I_{\rm C}$ = 1 A; $I_{\rm B}$ = 0.25 A; $T_{\rm lead}$ = 25°C	-	-	1	V
		$I_{\rm C}$ = 1.5 A; $I_{\rm B}$ = 0.5 A; $T_{\rm lead}$ = 25°C	-	-	1.5	V
V _{BEsat} base-em	base-emitter saturation	I _C = 0.5 A; I _B = 0.1 A; T _{lead} = 25°C	-	-	1	V
	voltage	I _C = 1 A; I _B = 0.25 A; T _{lead} = 25°C	-	-	1.2	V
V _F	forward voltage	$I_F = 0.5 \text{ A}; T_j = 25^{\circ}\text{C}$	-	-	1.5	V
h _{FE}	DC current gain	$I_{c} = 0.5 \text{ A}$; $V_{ce} = 2 \text{ V}$; $T_{j} = 25^{\circ}\text{C}$	8	17	25	
		$I_{c} = 1 \text{ A}$; $V_{ce} = 2 \text{ V}$; $T_{j} = 25^{\circ}\text{C}$	5	9	15	
Dynamic	characteristics	· · · · · ·				
t _{on}	turn-on time	$ \begin{array}{l} I_{C} = 1 \text{ A}; \ I_{Bon} = 0.2 \text{ A}; \ I_{Boff} = -0.2 \text{ A}; \\ R_{L} = 75 \ \Omega; \ T_{Iead} = 25 \ ^{\circ}\text{C}; \ resistive \ Ioad; \\ \hline Fig. 5; \ Fig. 6 \end{array} $	-	-	1	μs
t _s	storage time	$\begin{split} I_{C} &= 1 \text{ A}; I_{\text{Bon}} = 0.2 \text{ A}; I_{\text{Boff}} = -0.2 \text{ A}; \\ R_{L} &= 75 \Omega; T_{\text{lead}} = 25 ^{\circ}\text{C}; \text{ resistive load}; \\ \hline \text{Fig. 5}; \text{ Fig. 6} \end{split}$	-	-	4	μs
		$\begin{split} I_{C} &= 1 \text{ A}; \ I_{Bon} = 0.2 \text{ A}; \ V_{BB} = -5 \text{ V}; \\ L_{B} &= 1 \ \mu\text{H}; \ T_{Iead} = 25 \ ^{\circ}\text{C}; \ inductive \ Ioad; \\ \hline \hline Fig. \ 7; \ Fig. \ 8 \end{split}$	-	0.8	-	μs
t _f	fall time	$\begin{split} I_{C} &= 1 \text{ A}; \ I_{\text{Bon}} = 0.2 \text{ A}; \ I_{\text{Boff}} = -0.2 \text{ A}; \\ R_{L} &= 75 \ \Omega; \ T_{\text{lead}} = 25 \ ^{\circ}\text{C}; \ \text{resistive load}; \\ \hline \underline{\text{Fig. 5}; \ \underline{\text{Fig. 6}}} \end{split}$	-	-	0.7	μs
		$ \begin{array}{l} I_{C} = 0.5 \text{ A}; \ I_{Bon} = 0.1 \text{ A}; \ V_{BB} = -5 \text{ V}; \\ I_{B} = 1 \ \mu\text{H}; \ T_{lead} = 25 \ ^{\circ}\text{C}; \ \text{inductive load}; \\ \hline \hline Fig. \ 7; \ Fig. \ 8 \end{array} $	-	0.1	-	μs

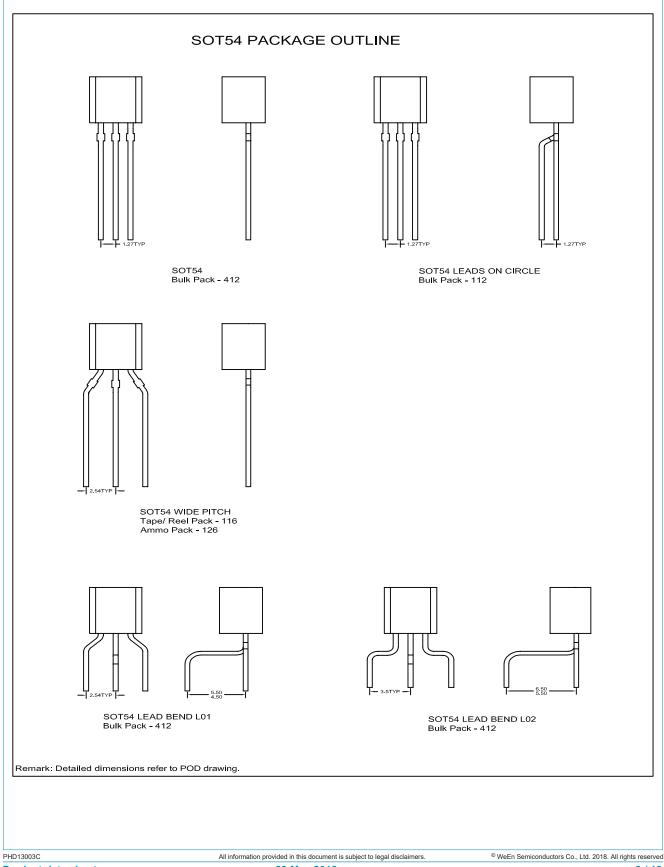
NPN power transistor with integrated diode



NPN power transistor with integrated diode



10. Package outline



11. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
PHD13003C v.2	20180224	Product data sheet	-	PHD13003C v.1	
Modifications:	Change from NXP version to WeEn version				
PHD13003C v.1	20100729	Product data sheet	-	-	

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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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